

Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

Parameter	Rating	Units
V_{DS}	1200	V
$I_D @ 25^\circ\text{C}$	117	A
$R_{DS(on)}$	16	m Ω



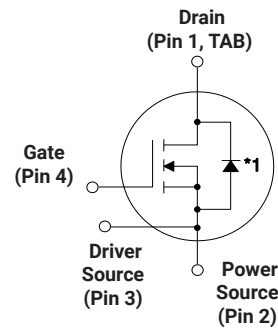
Applications

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating



Inner circuit

TO-247-4
Package



- (1) Drain
- (2) Power Source
- (3) Driver Source
- (4) Gate

*1 Body Diode

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
V_{GSmax}	Gate - Source Voltage (dynamic)	-10/+22	V	AC ($f > 1\text{ Hz}$)	
V_{GSop}	Gate - Source Voltage (static)	-5/+18	V	Static	
I_D	Continuous Drain Current	147	A	$V_{GS} = 15\text{ V}, T_c = 25^\circ\text{C}$	
		112		$V_{GS} = 15\text{ V}, T_c = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	250	A	Pulse width t_p limited by T_{jmax}	
P_D	Power Dissipation	555	W	$T_c = 25^\circ\text{C}, T_j = 175^\circ\text{C}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-40 to +175	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	1.6mm (0.063") from case for 10s	

Note (1): When using MOSFET Body Diode $V_{GSmax} = -4\text{V}/+19\text{V}$

Note (2): MOSFET can also safely operate at 0/+15 V



Electrical Characteristics (T_c = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V _{(BR)DSS}	Drain-Source Breakdown Voltage	1200			V	V _{GS} = 0 V, I _D = 100 μA	
V _{GS(th)}	Gate Threshold Voltage	1.8	2.9	3.6	V	V _{DS} = V _{GS} , I _D = 23 mA	
			2.1		V	V _{DS} = V _{GS} , I _D = 23 mA, T _J = 175°C	
I _{DSS}	Zero Gate Voltage Drain Current		1	100	μA	V _{DS} = 1200 V, V _{GS} = 0 V	
I _{GSS}	Gate-Source Leakage Current		10	100	nA	V _{GS} = 15 V, V _{DS} = 0 V	
R _{DS(on)}	Drain-Source On-State Resistance	11.2	16	22.3	mΩ	V _{GS} = 15 V, I _D = 75 A	
			22			V _{GS} = 15 V, I _D = 75 A, T _J = 175°C	
g _{fs}	Transconductance		58		S	V _{DS} = 20 V, I _{DS} = 75 A	
			47			V _{DS} = 20 V, I _{DS} = 75 A, T _J = 175°C	
C _{iss}	Input Capacitance		3815		pF	V _{GS} = 0 V, V _{DS} = 800 V f = 1 MHz V _{AC} = 25 mV	
C _{oss}	Output Capacitance		230				
C _{rss}	Reverse Transfer Capacitance		29				
E _{oss}	C _{oss} Stored Energy		130				
E _{ON}	Turn-On Switching Energy (SiC Diode FWD)		1.0		mJ	V _{DS} = 800 V, V _{GS} = -4 V/+15 V, I _D = 75 A, R _{G(ext)} = 2.5Ω, L = 65.7 μH, T _J = 175°C	
E _{OFF}	Turn Off Switching Energy (SiC Diode FWD)		0.8				
E _{ON}	Turn-On Switching Energy (Body Diode FWD)		2.3		mJ	V _{DS} = 800 V, V _{GS} = -4 V/+15 V, I _D = 75 A, R _{G(ext)} = 2.5Ω, L = 65.7 μH, T _J = 175°C	
E _{OFF}	Turn Off Switching Energy (Body Diode FWD)		0.6				
t _{d(on)}	Turn-On Delay Time		38		ns	V _{DD} = 800 V, V _{GS} = -4 V/15 V R _{G(ext)} = 2.5 Ω, I _D = 75 A, L = 65.7 Timing relative to V _{DS} , Inductive load	
t _r	Rise Time		30				
t _{d(off)}	Turn-Off Delay Time		84				
t _f	Fall Time		27				
R _{G(int)}	Internal Gate Resistance		2.6		Ω	f = 1 MHz, V _{AC} = 25 mV	
Q _{gs}	Gate to Source Charge		46		nC	V _{DS} = 800 V, V _{GS} = -4 V/15 V I _D = 75 A Per IEC60747-8-4 pg 21	
Q _{gd}	Gate to Drain Charge		100				
Q _g	Total Gate Charge		216				



Reverse Diode Characteristics (T_c = 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V _{SD}	Diode Forward Voltage	4.7		V	V _{GS} = -4 V, I _{SD} = 37.5 A, T _J = 25 °C	
		4.1		V	V _{GS} = -4 V, I _{SD} = 37.5 A, T _J = 175 °C	
I _S	Continuous Diode Forward Current		112	A	V _{GS} = -4 V, T _C = 25 °C	
I _{S, pulse}	Diode pulse Current		250	A	V _{GS} = -4 V, pulse width t _p limited by T _{Jmax}	
t _{rr}	Reverse Recover time	46		ns	V _{GS} = -4 V, I _{SD} = 75 A, V _R = 800 V dif/dt = 4000 A/μs, T _J = 175 °C	
Q _{rr}	Reverse Recovery Charge	1220		nC		
I _{rrm}	Peak Reverse Recovery Current	68		A		
t _{rr}	Reverse Recover time	42		ns	V _{GS} = -4 V, I _{SD} = 75 A, V _R = 800 V dif/dt = 5500 A/μs, T _J = 175 °C	
Q _{rr}	Reverse Recovery Charge	980		nC		
I _{rrm}	Peak Reverse Recovery Current	66		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
R _{θJC}	Thermal Resistance from Junction to Case	0.27	°C/W		
R _{θJA}	Thermal Resistance From Junction to Ambient	40			

Package Dimensions

Unit: mm

